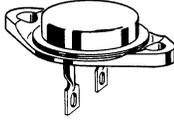


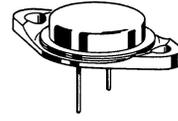
2N1651 thru 2N1653 (Germanium)

2N2285 thru 2N2287 (Germanium)



CASE 161
(TO-41)

2N1651 thru 2N1653
Collector connected to case



CASE 3A
(TO-3 modified)

2N2285 thru 2N2287

PNP Germanium power transistors designed for high-current switching applications requiring low saturation voltages and fast switching times in addition to good safe operating area.

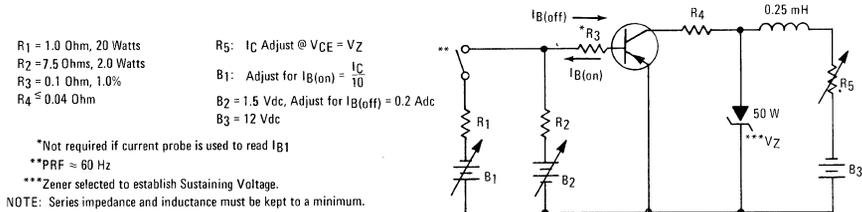
MAXIMUM RATINGS

Rating	Symbol	2N1651 2N2285	2N1652 2N2286	2N1653 2N2287	Unit
Collector-Emitter Voltage	V_{CEO}	30	60	80	Vdc
Collector-Base Voltage	V_{CB}	60	100	120	Vdc
Emitter-Base Voltage	V_{EB}	←	1.5	→	Vdc
Collector Current - Continuous	I_C	←	25	→	Adc
Base Current - Continuous	I_B	←	5.0	→	Adc
Total Device Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	←	106 1.25	→	Watts W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	←	-65 to +110	→	$^\circ C$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	0.8	$^\circ C/W$

FIGURE 1 – SUSTAINING VOLTAGE TEST CIRCUIT



2N1651 thru 2N1653/2N2285 thru 2N2287 (continued)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100\text{ mAdc}$, $I_B = 0$)	BV_{CEO}	30 60 80	- - -	Vdc
Collector-Emitter Sustaining Voltage (See Figure 1) ($I_C = 25\text{ Adc}$)	$V_{CE(sus)}$	40 45 50	- - -	Vdc
Collector Cutoff Current ($V_{CB} = 2.0\text{ Vdc}$, $I_E = 0$)	I_{CBO1}	-	200	μAdc
Collector Cutoff Current ($V_{CB} = 40\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$)	I_{CBO2}	- - -	5.0 5.0 5.0	mAdc
Collector Cutoff Current ($V_{CB} = 40\text{ Vdc}$, $I_E = 0$, $T_C = 100^\circ\text{C}$) (+0, -3.0°C) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$, $T_C = 100^\circ\text{C}$) (+0, -3.0°C) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$, $T_C = 100^\circ\text{C}$) (+0, -3.0°C)	I_{CBO3}	- - -	35 35 35	mAdc
Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 120\text{ Vdc}$, $I_E = 0$)	I_{CBO4}	- - -	20 20 20	mAdc
Emitter Cutoff Current ($V_{EB} = 1.5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	50	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{ Adc}$, $V_{CE} = 2.0\text{ Vdc}$) ($I_C = 25\text{ Adc}$, $V_{CE} = 1.5\text{ Vdc}$)	h_{FE}	35 20	140 -	-
Collector-Emitter Saturation Voltage ($I_C = 25\text{ Adc}$, $I_B = 2.5\text{ Adc}$)	$V_{CE(sat)}$	-	0.30	Vdc
Base-Emitter Saturation Voltage ($I_C = 25\text{ Adc}$, $I_B = 2.5\text{ Adc}$)	$V_{BE(sat)}$	-	0.65	Vdc

SMALL-SIGNAL CHARACTERISTICS

Small-Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 6.0\text{ Vdc}$, $f = 30\text{ kHz}$)	h_{fe}	20	-	-
---	----------	----	---	---

SWITCHING CHARACTERISTICS

Rise Time	$(I_C = 25\text{ Adc}, I_{B(on)} = 2.5\text{ Adc}, I_{B(off)} = 2.5\text{ Adc})$ (See Figure 2)	t_r	-	12	μs
Storage Time		t_s	-	10	μs
Fall Time		t_f	-	8.0	μs

FIGURE 2 – SWITCHING TIME TEST CIRCUIT

